

RELIABILITY MONITOR

PRODUCT	MONITOR DATE	DATE CODE	ASSEMBLY FACILITY	ASSEMBLY LOT NO	PROCESS TYPE	PACKAGE TYPE
DS1669	Nov-96	9642 B3	OMEDATA	DD628106AAA	1.2μ OX/NI EEPROM	08 SOIC 200

STRESS/JOB NO.

**READPOINT
(Sample Size/No. of Fails)**

Preconditioning (P/C):
HTC Vapor Phase
P-18594

<u>Electrical</u>	<u>Cum %</u>
235/5	2.1%
F1,F2,F3	

Infant / High Voltage Life **
125°C, 7.0 V.
P-18638, P-18638

<u>48 Hr</u>	<u>336 Hr</u>	<u>1KHr</u>	<u>*Failure Rate</u>
226/0	77/0		

*Chi Squared Method, 60% C. L., 55°C & 5.5V; Temperature Derating: Ea = 0.7 ev; Voltage Derating B = 1.0

** with Write Cycle Program stress = 60~/hr/cell

Temp Cycle
-55°C to +125°C
P-18733

<u>300 ~</u>	<u>1K ~</u>	<u>Cum %</u>
36/0		

Biased Moisture
85°C/85% RH, 5.5 V.
P-18734

<u>274 Hr</u>	<u>959 Hr</u>	<u>Cum %</u>
70/0		

Storage Life
150°C, No bias
P-18735

<u>336 Hr</u>	<u>1KHr</u>	<u>Cum %</u>
38/0		

Failure Mode

F1: 1-Continuity
F2: 2-Icc Stdby
F3: 2-IIH Lkg

Failure Analysis

960393, Input junction leakage due to ESD.
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